

## STGWA80H65DFBAG-VB Datasheet

### 600V Trench and Fieldstop IGBT

PRODUCT SUMMARY		
V <sub>CE</sub> (V)	600	
I <sub>C</sub> (A)	160 (T <sub>C</sub> =25 °C)	80 (T <sub>C</sub> =100 °C)
V <sub>CE (sat)</sub> (V)	1.8	
I <sub>CM</sub> (A)	240	

#### FEATURES

- Very Low V<sub>CEsat</sub>
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge (Q<sub>g</sub>)
- Avalanche energy rated (UIS)



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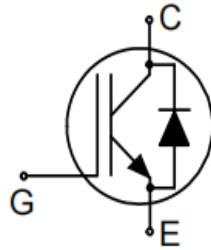
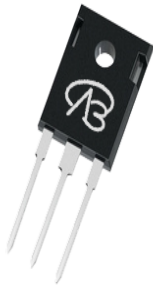
#### APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers
- Renewable energy
  - Solar (PV inverters)
- Switch mode power supplies (SMPS)

#### Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter

TO-247



Top View

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Collector-Emitter Voltage		V <sub>CE</sub>	600	V	
Gate-Emitter Voltage		V <sub>GE</sub>	±30		
Continuous Collector Current (T <sub>J</sub> = 150 °C)	V <sub>GE</sub> at 15 V	I <sub>C</sub>	T <sub>C</sub> = 25 °C	160	A
			T <sub>C</sub> = 100 °C	80	
Pulsed Collector Current <sup>a</sup>		I <sub>CM</sub>	240		
Diode Forward Current <sup>b</sup>		I <sub>F</sub>	80	A	
Maximum Power Dissipation		P <sub>D</sub>	T <sub>C</sub> = 25 °C	340	W
			T <sub>C</sub> = 100 °C	180	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Short Circuit Withstand Time <sup>TC=150</sup>	V <sub>GE</sub> = 15V, V <sub>CE</sub> 400V	t <sub>sc</sub>	3	μs	
Short Circuit Withstand Time <sup>TC=100</sup>	V <sub>GE</sub> = 15V, V <sub>CE</sub> 330V		5		
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s		260	°C	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- Current limited by maximum junction temperature.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case	$R_{thJC}$	-	0.5	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Collector-Emitter Breakdown Voltage	$BV_{CE}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$ $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$		600 600	- -	- -	V
Gate-Source Threshold Voltage (N)	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_D = 250\text{ }\mu\text{A}$		4	5	6	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_J = 25\text{ }^\circ\text{C}$		-	1	20	$\mu\text{A}$
		$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	1000	-	$\mu\text{A}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GS} = \pm 2\text{ V}$		-	-	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}$	$I_C = 80\text{ A}$	-	1.8	2.1	V
Forward Transconductance	$g_{fs}$	$V_{CE} = 20\text{ V}, I_C = 80\text{ A}$		-	17	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{ies}$	$V_{GE} = 0\text{ V}, V_{CE} = 25\text{ V},$ $f = 500\text{ KHz}$		-	8200	-	pF
Output Capacitance	$C_{oes}$			-	210	-	
Reverse Transfer Capacitance	$C_{res}$			-	165	-	
Turn-on Energy	$E_{on}$	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 80\text{ A}, R_g = 10\text{ }\Omega$		-	22	-	nJ
Turn-off Energy	$E_{off}$			-	1.5	-	
Total Gate Charge	$Q_g$	$V_{GE} = 20\text{ V}$	$I_C = 80\text{ A}, V_{CE} = 400\text{ V}$	-	280	-	nC
Gate-Emitter Charge	$Q_{ge}$			-	82	-	
Gate to Collector Charge	$Q_{gc}$			-	115	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 80\text{ A}, R_g = 10\text{ }\Omega$		-	92	-	ns
Rise Time	$t_r$			-	50	-	
Turn-Off Delay Time	$t_{d(off)}$			-	154	-	
Fall Time	$t_f$			-	28	-	
Internal emitter inductance measured 5 mm	$L_E$			-	13	-	
<b>Diode Characteristics</b>							
Diode Forward Current	$I_F$	IGBT symbol showing the integral reverse junction diode		-	-	80	A
Pulsed Diode Forward Current	$I_{FM}$			-	-	240	
Diode Forward Voltage	$V_F$	$I_F = 80\text{ A}$		-	1.52	2.0	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 80\text{ A},$ $dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	73	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	0.51	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	9	-	A

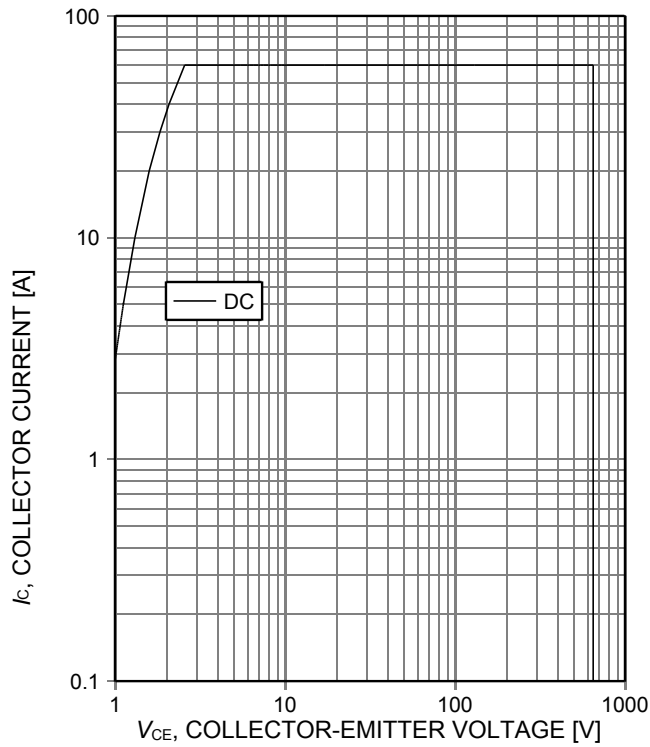


Figure 1. **Forward bias safe operating area**  
( $D=0$ ,  $T_C=25^\circ\text{C}$ ,  $T_{vj}\leq 175^\circ\text{C}$ ;  $V_{GE}=15\text{V}$ .  
Recommended use at  $V_{GE}\geq 7.5\text{V}$ )

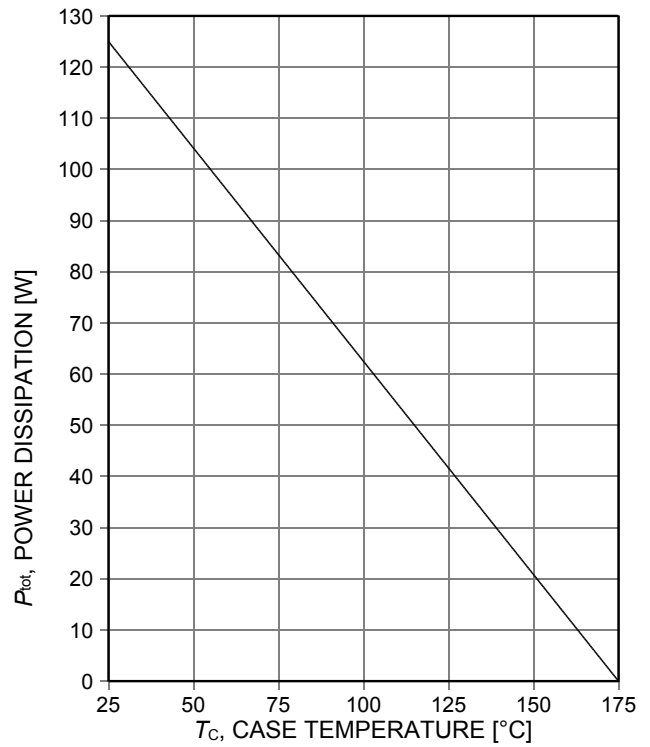


Figure 2. **Power dissipation as a function of case temperature**  
( $T_{vj}\leq 175^\circ\text{C}$ )



Figure 3. **Collector current as a function of case temperature**



Figure 4. **Typical output characteristic**



Figure 5. Typical output characteristic ( $T_{vj}=150^{\circ}\text{C}$ )



Figure 6. Typical transfer characteristic ( $V_{CE}=20\text{V}$ )



Figure 7. Typical collector-emitter saturation voltage as a function of junction temperature



Figure 8. Typical switching times as a function of collector current

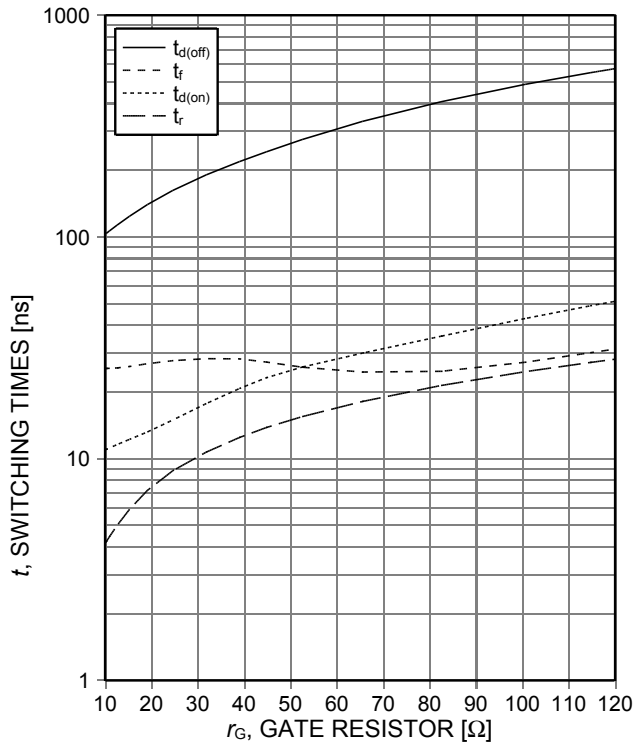


Figure 9. Typical switching times as a function of gate resistor



Figure 10. Typical switching times as a function of junction temperature

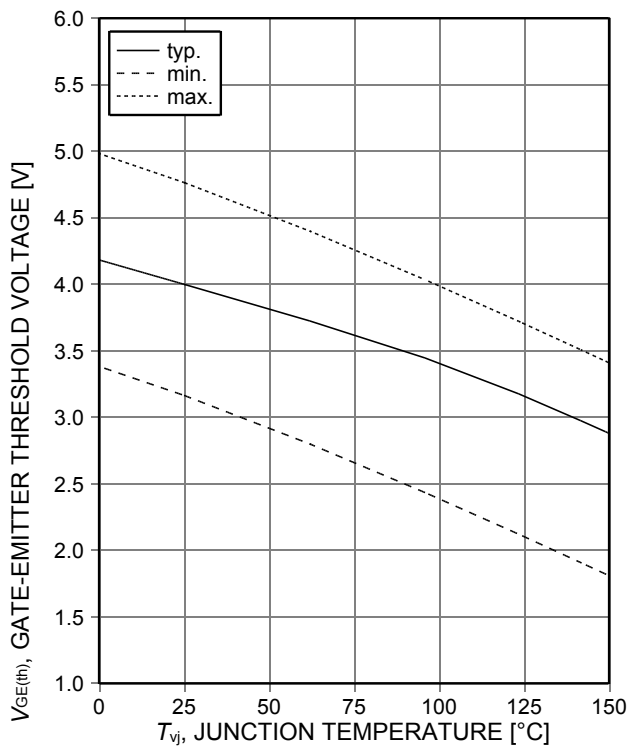


Figure 11. Gate-emitter threshold voltage as a function of junction temperature

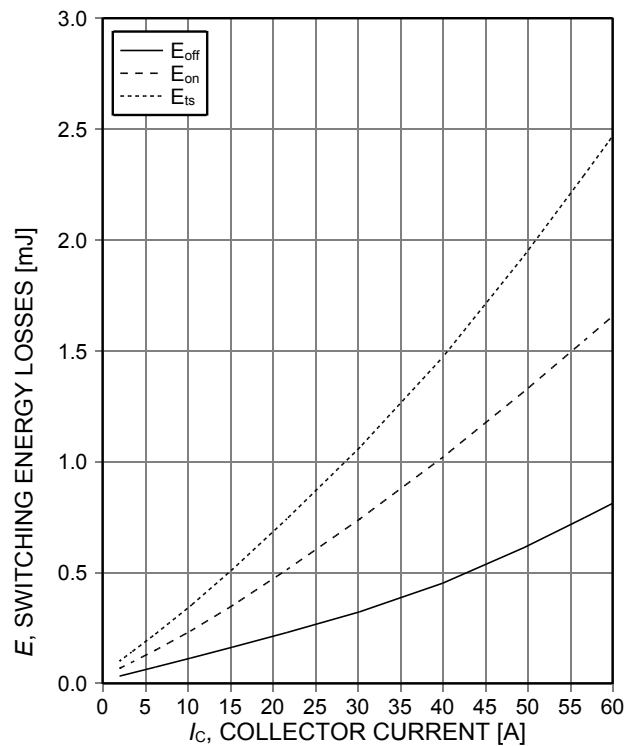


Figure 12. Typical switching energy losses as a function of collector current



Figure 13. Typical switching energy losses as a function of gate resistor



Figure 14. Typical switching energy losses as a function of junction temperature



Figure 15. Typical switching energy losses as a function of collector emitter voltage



Figure 16. Typical gate charge



Figure 17. Typical capacitance as a function of collector-emitter voltage



Figure 18. IGBT transient thermal impedance



Figure 19. Diode transient thermal impedance as a function of pulse width

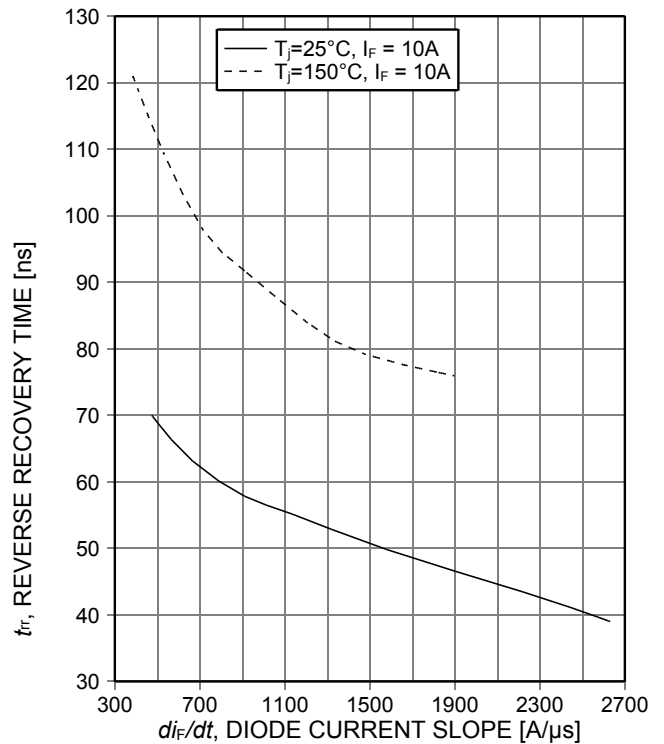


Figure 20. Typical reverse recovery time as a function of diode current slope



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